

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	12	(US-20020096733-\$) did. or (US-5625210-\$ or US-5841176-\$ or US-5933190-\$ or US-6204524-\$ or US-6326652-\$ or US-6333205-\$ or US-6376868-\$ or US-6445014-\$ or US-6617174-\$ or US-6740915-\$ or US-6835637-\$) did.	US-PGP UB; USPAT	OR	OFF	2005/08/17 08:37
L9	6	"893998".ap.	US-PGP UB; USPAT	OR	OFF	2005/08/17 09:22
L11	1602	(438/57,87,275).CCLS.	US-PGP UB; USPAT; USOCR	OR	OFF	2005/08/17 09:24
S1	1	("20040217394").PN.	US-PGP UB; USPAT; USOCR	OR	OFF	2005/08/16 11:44
S2	45954	(etching etched etch) near3 (wet-etching hydrofluoric acid HF buffered adj oxide adj etchant BOE)	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2005/08/16 13:53
S3	3	(etching etched etch) near5 wet-etching near4 (hydrofluoric HF) near4 (buffered adj oxide adj etchant BOE)	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2005/08/16 11:52

S4	892	mask near (removing removal) with thinner sulfuric with plasma	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2005/08/16 11:52
S5	0	mask near (removing removal) with thinner with sulfuric with plasma	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2005/08/16 11:52
S6	3	mask near (removing removal) with (thinner sulfuric) with plasma	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2005/08/16 11:58
S7	83614	substrate and epitaxial andd CMOS adj imager and (mask resist) and pixel and logic and photodiode	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2005/08/16 11:59
S8	99	substrate and epitaxial and CMOS adj imager and (mask resist) and pixel and logic and photodiode	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2005/08/16 11:59

S9	99	substrate and epitaxial and CMOS adj imager and (mask resist) and pixel and logic and photodiode	US-PGP UB; USPAT; USOCR	OR	OFF	2005/08/16 12:01
S10	84	substrate and epitaxial and CMOS adj imager and (mask resist) and pixel and logic and photodiode and rhodes.in.	US-PGP UB; USPAT; USOCR	OR	OFF	2005/08/16 12:53
S11	14	substrate and epitaxial and CMOS adj imager and (mask resist) and pixel and peripheral with logic and photodiode and rhodes.in.	US-PGP UB; USPAT; USOCR	OR	OFF	2005/08/16 12:13
S12	117	CMOS adj imager and (mask resist) and pixel and logic and photodiode	US-PGP UB; USPAT; USOCR	OR	OFF	2005/08/16 13:04
S13	76	S12 and (field adj oxide fox)	US-PGP UB; USPAT; USOCR	OR	OFF	2005/08/16 13:04
S14	16	("4374700"   "5319604"   "5461425"   "5471515"   "5541402"   "5576763"   "5612799"   "5614744"   "5625210"   "5705846"   "5708263"   "5739562"   "5757045"   "6023081"   "6040593"   "6160282"). PN.	US-PGP UB; USPAT; USOCR	OR	OFF	2005/08/16 13:16
S15	76	"5614744" and oxide	US-PGP UB; USPAT; USOCR	OR	OFF	2005/08/16 14:26
S16	1	S1 and (insulator oxide dielectric) near gate	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2005/08/16 15:29

S17	43	"5614744" and (insulator oxide dielectric) near gate	US-PGP UB; USPAT; USOCR	OR	OFF	2005/08/16 15:06
S18	4	((("5,962,856") or ("6,169,286") or ("5,780,858") or ("5,134,489"))).PN.	US-PGP UB; USPAT; USOCR	OR	OFF	2005/08/16 15:07
S19	1	S18 and (insulator oxide dielectric) near gate	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2005/08/16 15:35
S20	2	S18 and (insulator oxide dielectric) not S19	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2005/08/16 15:38
S21	1	S18 not (S19 or S20)	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	OFF	2005/08/16 15:38
S22	11	cmos adj (image imager imaging) and (dual double) near3 (dielectric insulator insulating oxide insulated)	US-PGP UB; USPAT	OR	ON	2005/08/16 15:57
S23	5	cmos adj (image imager imaging) and Leland adj Stanford	US-PGP UB; USPAT	OR	ON	2005/08/16 15:54

S24	5	cmos adj (image imager imaging) and Leland adj Stanford	US-PGP UB; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/08/16 15:54
S25	13	cmos adj (image imager imaging) and (dual double) near3 (dielectric insulator insulating oxide insulated)	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWEN T	OR	ON	2005/08/16 16:00
S29	2	cmos adj (image imager imaging) and (DGO Dual adj Gate adj Oxide)	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/08/16 16:08
S30	232	cmos and (DGO Dual adj Gate adj Oxide)	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/08/16 16:09